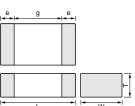
Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

High Dielectric Constant Type 6.3/16/25/50V





Part Number		Dir	nensions (n	าm)		
	L	W	Т	е	g min.	
GRM155	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4	
GRM188*	1.6 ±0.1	0.8 ±0.1	0.8 ±0.1	0.2 to 0.5	0.5	
GRM216			0.6 ±0.1		0.7	
GRM219	2.0 ±0.1	1.25 ±0.1	0.85 ±0.1	0.2 to 0.7		
GRM21B			1.25 ±0.1			
GRM319	2 2 40 15	1.6 ±0.15	0.85 ±0.1			
GRM31M	3.∠ ±0.15	1.0 ±0.15	1.15 ±0.1	0.3 to 0.8	1.5	
GRM31C	3.2 ±0.2	1.6 ±0.2	1.6 ±0.2			

* Bulk Case : 1.6 ±0.07(L)×0.8 ±0.07(W)×0.8 ±0.07(T)

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R61A683KA01	X5R (EIA)	10	68000pF±10%	1.0	0.5	0.50
GRM155R61A104KA01	X5R (EIA)	10	0.1µF±10%	1.0	0.5	0.50
GRM188R61A334KA61	X5R (EIA)	10	0.33 μF±10%	1.6	0.8	0.80
GRM188R61A474KA61	X5R (EIA)	10	0.47µF±10%	1.6	0.8	0.80
GRM188R61A684KA61	X5R (EIA)	10	0.68µF±10%	1.6	0.8	0.80
GRM188R61A105KA61	X5R (EIA)	10	1μF ±10%	1.6	0.8	0.80
GRM188R60J105KA01	X5R (EIA)	6.3	1μF ±10%	1.6	0.8	0.80
GRM219R61A105KC01	X5R (EIA)	10	1μF ±10%	2.0	1.25	0.90
GRM21BR61A225KA01	X5R (EIA)	10	2.2μF ±10%	2.0	1.25	1.25
GRM219R60J155KC01	X5R (EIA)	6.3	1.5μF ±10%	2.0	1.25	0.90
GRM21BR60J225KA01	X5R (EIA)	6.3	2.2μF ±10%	2.0	1.25	1.25
GRM21BR60J335KA11	X5R (EIA)	6.3	3.3µF ±10%	2.0	1.25	1.25
GRM21BR60J475KA11	X5R (EIA)	6.3	4.7μF ±10%	2.0	1.25	1.25
GRM319R61A225KC01	X5R (EIA)	10	2.2μF ±10%	3.2	1.6	0.90
GRM31XR61A335KC12	X5R (EIA)	10	3.3µF ±10%	3.2	1.6	1.30
GRM31CR61A475KA01	X5R (EIA)	10	4.7μF ±10%	3.2	1.6	1.60
GRM31MR60J475KC11	X5R (EIA)	6.3	4.7μF ±10%	3.2	1.6	1.15
GRM31CR61A106KA01	X5R (EIA)	10	10μF ±10%	3.2	1.6	1.60
GRM31CR60J106KA01	X5R (EIA)	6.3	10μF ±10%	3.2	1.6	1.60
GRM31CR60J226ME20	X5R (EIA)	6.3	22μF ±20%	3.2	1.6	1.60
GRM32ER61A106KC01	X5R (EIA)	10	10μF ±10%	3.2	2.5	2.50
GRM55DR61H106KA01	X5R (EIA)	50	10μF ±10%	5.7	5.0	2.00
GRM15XR71H221KA86	X7R (EIA)	50	220pF±10%	1.0	0.5	0.25
GRM155R71H221KA01	X7R (EIA)	50	220pF±10%	1.0	0.5	0.50
GRM15XR71H331KA86	X7R (EIA)	50	330pF±10%	1.0	0.5	0.25
GRM155R71H331KA01	X7R (EIA)	50	330pF±10%	1.0	0.5	0.50
GRM15XR71H471KA86	X7R (EIA)	50	470pF±10%	1.0	0.5	0.25
GRM155R71H471KA01	X7R (EIA)	50	470pF±10%	1.0	0.5	0.50
GRM15XR71H681KA86	X7R (EIA)	50	680pF±10%	1.0	0.5	0.25
GRM155R71H681KA01	X7R (EIA)	50	680pF±10%	1.0	0.5	0.50
GRM15XR71H102KA86	X7R (EIA)	50	1000pF±10%	1.0	0.5	0.25
GRM155R71H102KA01	X7R (EIA)	50	1000pF±10%	1.0	0.5	0.50
GRM15XR71H152KA86	X7R (EIA)	50	1500pF±10%	1.0	0.5	0.25
GRM155R71H152KA01	X7R (EIA)	50	1500pF±10%	1.0	0.5	0.50
GRM155R71H222KA01	X7R (EIA)	50	2200pF±10%	1.0	0.5	0.50

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Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R71H332KA01	X7R (EIA)	50	3300pF±10%	1.0	0.5	0.50
GRM155R71H472KA01	X7R (EIA)	50	4700pF±10%	1.0	0.5	0.50
GRM15XR71E182KA86	X7R (EIA)	25	1800pF±10%	1.0	0.5	0.25
GRM15XR71E222KA86	X7R (EIA)	25	2200pF±10%	1.0	0.5	0.25
GRM155R71E682KA01	X7R (EIA)	25	6800pF±10%	1.0	0.5	0.50
GRM155R71E103KA01	X7R (EIA)	25	10000pF±10%	1.0	0.5	0.50
GRM15XR71C332KA86	X7R (EIA)	16	3300pF±10%	1.0	0.5	0.25
GRM15XR71C472KA86	X7R (EIA)	16	4700pF±10%	1.0	0.5	0.25
GRM15XR71C682KA86	X7R (EIA)	16	6800pF±10%	1.0	0.5	0.25
GRM155R71C153KA01	X7R (EIA)	16	15000pF±10%	1.0	0.5	0.50
GRM155R71C223KA01	X7R (EIA)	16	22000pF±10%	1.0	0.5	0.50
GRM155R71A333KA01	X7R (EIA)	10	33000pF±10%	1.0	0.5	0.50
GRM155R71A473KA01	X7R (EIA)	10	, 47000pF±10%	1.0	0.5	0.50
GRM188R71H221KA01	X7R (EIA)	50	220pF±10%	1.6	0.8	0.80
GRM188R71H331KA01	X7R (EIA)	50	330pF±10%	1.6	0.8	0.80
GRM188R71H471KA01	X7R (EIA)	50	470pF±10%	1.6	0.8	0.80
GRM188R71H681KA01	X7R (EIA) X7R (EIA)	50	680pF±10%	1.6	0.8	0.80
GRM188R71H102KA01	X7R (EIA) X7R (EIA)	50	1000pF±10%	1.6	0.8	0.80
GRM188R71H152KA01	X7R (EIA) X7R (EIA)	50	1500pF±10%	1.6	0.8	0.80
GRM188R71H152KA01	X7R (EIA) X7R (EIA)	50	2200pF±10%	1.6	0.8	0.80
GRM188R71H332KA01	X7R (EIA)	50	3300pF±10%	1.6	0.8	0.80
GRM188R71H472KA01	X7R (EIA)	50	4700pF±10%	1.6	0.8	0.80
GRM188R71H682KA01	X7R (EIA)	50	6800pF±10%	1.6	0.8	0.80
GRM188R71H103KA01	X7R (EIA)	50	10000pF±10%	1.6	0.8	0.80
GRM188R71H153KA01	X7R (EIA)	50	15000pF±10%	1.6	0.8	0.80
RM188R71H223KA01	X7R (EIA)	50	22000pF±10%	1.6	0.8	0.80
RM188R71E333KA01	X7R (EIA)	25	33000pF±10%	1.6	0.8	0.80
GRM188R71E473KA01	X7R (EIA)	25	47000pF±10%	1.6	0.8	0.80
RM188R71E683KA01	X7R (EIA)	25	68000pF±10%	1.6	0.8	0.80
GRM188R71E104KA01	X7R (EIA)	25	0.1µF±10%	1.6	0.8	0.80
GRM188R71C104KA01	X7R (EIA)	16	0.1µF±10%	1.6	0.8	0.80
GRM188R71A154KA01	X7R (EIA)	10	0.15µF±10%	1.6	0.8	0.80
GRM188R71A224KA01	X7R (EIA)	10	22000pF±10%	1.6	0.8	0.80
GRM219R71H333KA01	X7R (EIA)	50	33000pF±10%	2.0	1.25	0.90
GRM21BR71H473KA01	X7R (EIA)	50	47000pF±10%	2.0	1.25	1.25
GRM21BR71H683KA01	X7R (EIA)	50	68000pF±10%	2.0	1.25	1.25
GRM21BR71H104KA01	X7R (EIA)	50	0.1µF±10%	2.0	1.25	1.25
GRM21BR71H154KA01	X7R (EIA)	50	0.15µF±10%	2.0	1.25	1.25
GRM21BR71H224KA01	X7R (EIA)	50	22000pF±10%	2.0	1.25	1.25
GRM21BR71E104KA01	X7R (EIA)	25	0.1µF±10%	2.0	1.25	1.25
GRM21BR71E154KA01	X7R (EIA)	25	0.15μF±10%	2.0	1.25	1.25
GRM219R71E224KC01	X7R (EIA)	25	22000pF±10%	2.0	1.25	0.90
GRM21BR71E334KC01	X7R (EIA)	25	0.33 μF±10%	2.0	1.25	1.25
GRM21BR71E474KC01	X7R (EIA)	25	0.47μF±10%	2.0	1.25	1.25
GRM219R71C474KC01	X7R (EIA)	16	0.47µF±10%	2.0	1.25	0.90
RM219R71C684KC01	X7R (EIA)	16	0.68µF±10%	2.0	1.25	0.90
RM21BR71C105KA01	X7R (EIA)	16	1μF ±10%	2.0	1.25	1.25
RM319R71H334KA01	X7R (EIA)	50	0.33 μF±10%	3.2	1.6	0.90
GRM31MR71H474KA01	X7R (EIA)	50	0.47μF±10%	3.2	1.6	1.15
GRM319R71E684KC01	X7R (EIA)	25	0.68μF±10%	3.2	1.6	0.90
GRM319R71E105KC01	X7R (EIA) X7R (EIA)	25	0.88μF±10% 1μF ±10%	3.2	1.6	1.15
	X7R (EIA) X7R (EIA)	16	1μF ±10%	3.2	1.6	0.90
GRM319R71C105KC11						
GRM31MR71C155KC11	X7R (EIA)	16	1.5μF ±10%	3.2	1.6	1.15
GRM31MR71C225KA35	X7R (EIA)	16	2.2μF ±10%	3.2	1.6	1.15

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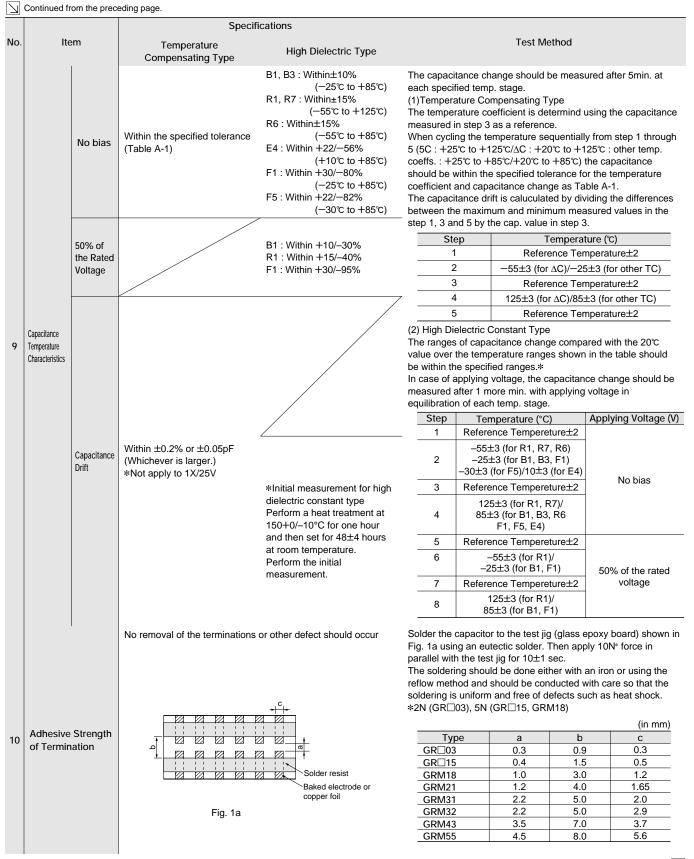
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Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM319R71A225KA01	X7R (EIA)	10	2.2μF ±10%	3.2	1.6	0.90
GRM32NR71H684KA01	X7R (EIA)	50	0.68µF±10%	3.2	2.5	1.35
GRM32RR71H105KA01	X7R (EIA)	50	1μF ±10%	3.2	2.5	1.80
GRM32RR71E225KC01	X7R (EIA)	25	2.2μF ±10%	3.2	2.5	1.80
GRM32MR71C225KC01	X7R (EIA)	16	2.2μF ±10%	3.2	2.5	1.15
GRM32NR71C335KC01	X7R (EIA)	16	3.3µF ±10%	3.2	2.5	1.35
GRM32RR71C475KC01	X7R (EIA)	16	4.7μF ±10%	3.2	2.5	1.80
GRM43ER71H225KA01	X7R (EIA)	50	2.2μF ±10%	4.5	3.2	2.50
GRM55RR71H105KA01	X7R (EIA)	50	1μF ±10%	5.7	5.0	1.80
GRM55RR71H155KA01	X7R (EIA)	50	1.5μF ±10%	5.7	5.0	1.80
GRM155F51H222ZA01	Y5V (EIA)	50	2200pF +80%, -20%	1.0	0.5	0.50
GRM155F51H472ZA01	Y5V (EIA)	50	4700pF +80%, -20%	1.0	0.5	0.50
GRM155F51H103ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.0	0.5	0.50
	Y5V (EIA)		•			0.50
GRM155F51E223ZA01 GRM155F51C473ZA01		25	22000pF +80%, -20%	1.0	0.5	
	Y5V (EIA)	16	47000pF +80%, -20%	1.0	0.5	0.50
GRM155F51C104ZA01	Y5V (EIA)	16	10000pF +80%, -20%	1.0	0.5	0.50
GRM188F51H103ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H223ZA01	Y5V (EIA)	50	22000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H473ZA01	Y5V (EIA)	50	47000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H104ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51E104ZA01	Y5V (EIA)	25	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51C224ZA01	Y5V (EIA)	16	22000pF +80%, -20%	1.6	0.8	0.80
GRM188F51C474ZA01	Y5V (EIA)	16	0.47µF +80%, -20%	1.6	0.8	0.80
GRM188F51A474ZC01	Y5V (EIA)	10	0.47µF +80%, -20%	1.6	0.8	0.80
GRM188F51A105ZA01	Y5V (EIA)	10	1µF +80%, -20%	1.6	0.8	0.80
GRM219F51H104ZA01	Y5V (EIA)	50	10000pF +80%, -20%	2.0	1.25	0.90
GRM21BF51H224ZA01	Y5V (EIA)	50	22000pF +80%, -20%	2.0	1.25	1.25
GRM219F51E224ZA01	Y5V (EIA)	25	22000pF +80%, -20%	2.0	1.25	0.90
GRM21BF51E474ZA01	Y5V (EIA)	25	0.47µF +80%, -20%	2.0	1.25	1.25
GRM219F51E105ZA01	Y5V (EIA)	25	1μF +80%, -20%	2.0	1.25	0.90
GRM21BF51E225ZA01	Y5V (EIA)	25	2.2µF +80%, -20%	2.0	1.25	1.25
GRM219F51C105ZA01	Y5V (EIA)	16	1μF +80%, -20%	2.0	1.25	0.90
GRM21BF51C225ZA01	Y5V (EIA)	16	2.2μF +80%, -20%	2.0	1.25	1.25
GRM219F51A105ZA01	Y5V (EIA)	10	1μF +80%, -20%	2.0	1.25	0.90
GRM21BF51A225ZA01	Y5V (EIA)	10	2.2μF +80%, -20%	2.0	1.25	1.25
GRM21BF51A475ZA01		10	4.7μF +80%, -20%	2.0	1.25	1.25
	Y5V (EIA)					1.25
GRM31MF51H474ZA01	Y5V (EIA)	50	0.47μF +80%, -20%	3.2	1.6	
GRM31MF51E105ZA01	Y5V (EIA)	25	1μF +80%, -20%	3.2	1.6	1.15
GRM31MF51E475ZA01	Y5V (EIA)	25	4.7μF +80%, -20%	3.2	1.6	1.15
GRM319F51C105ZA01	Y5V (EIA)	16	1μF +80%, -20%	3.2	1.6	0.90
GRM31MF51C225ZA01	Y5V (EIA)	16	2.2µF +80%, -20%	3.2	1.6	1.15
GRM31MF51C475ZA12	Y5V (EIA)	16	4.7μF +80%, -20%	3.2	1.6	1.15
GRM319F51A225ZA01	Y5V (EIA)	10	2.2µF +80%, -20%	3.2	1.6	0.90
GRM31MF51A475ZA01	Y5V (EIA)	10	4.7µF +80%, -20%	3.2	1.6	1.15
GRM31MF51A106ZA01	Y5V (EIA)	10	10µF +80%, -20%	3.2	1.6	1.15
GRM31MF50J106ZA01	Y5V (EIA)	6.3	10µF +80%, -20%	3.2	1.6	1.15
GRM32RF51H105ZA01	Y5V (EIA)	50	1µF +80%, -20%	3.2	2.5	1.80
GRM329F51E475ZA01	Y5V (EIA)	25	4.7µF +80%, -20%	3.2	2.5	0.90
GRM32NF51E106ZA01	Y5V (EIA)	25	10µF +80%, -20%	3.2	2.5	1.35
GRM32NF51C106ZA01	Y5V (EIA)	16	10µF +80%, -20%	3.2	2.5	1.35
GRM188E41H103MA01	Z5U (EIA)	50	10000pF±20%	1.6	0.8	0.80
GRM188E41H223MA01	Z5U (EIA)	50	22000pF±20%	1.6	0.8	0.80
GRM216E41H473MA01	Z5U (EIA)	50	47000pF±20%	2.0	1.25	0.60
GRM219E41H104MA01	Z5U (EIA)	50	10000pF±20%	2.0	1.25	0.90
	Z5U (EIA)	50	22000pF±20%	3.2	1.6	0.90

■ Specifications and Test Methods

		Specifi	cations				
No.	Item	Temperature Compensating Type	High Dielectric Type		Test	Method	
1	Operating Temperature Range	−55 to +125℃	B1, B3, F1 : -25°C to +85°C R1, R7 : -55°C to +125°C E4 : +10°C to +85°C F5 : -30°C to +85°C	Reference Temperature : 25℃ (2∆, 3∆, 4∆, B1, B3, F1, R1 : 20℃)			
2	Rated Voltage	See the previous pages		may be applie When AC volta	arger, should be	o the capacitor. osed on DC vol	tage, V ^{p.p} or V ^{o.p} ,
3	Appearance	No defects or abnormalities		Visual inspect	ion		
4	Dimensions	Within the specified dimensions	Using calipers				
5	Dielectric Strength	No defects or abnormalities		No failure should be observed when 300% of the rated voltage (temperature compensating type) or 250% of the rated voltage (high dielectric constant type) is applied between the terminations for 1 to 5 seconds, provided the charge/discharge current is less than 50mA.			
6	Insulation Resistance	C≦0.047μF : More than 10,000l C>0.047μF : 500Ω • F	MΩ C : Nominal Capacitance	voltage not ex 75%RH max.	resistance shou ceeding the rate and within 2 min rge current is les	d voltage at 20 outes of chargin	℃/25℃ and
7	Capacitance	Within the specified tolerance					20℃/25℃ at the
8	Q/ Dissipation Factor (D.F.)	30pF and over : Q≥1000 30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	$\begin{array}{l} [B1, B3, R1, R6, R7, E4] \\ W.V.: 25Vmin.: 0.025max. \\ W.V.: 16/10V: 0.035max. \\ W.V.: 6.3V/4V \\ : 0.05max. (C<3.3\muF) \\ : 0.1max. (C\geq3.3\muF) \\ [F1, F5] \\ W.V.: 25Vmin. \\ : 0.05max. (C<0.1\muF) \\ : 0.09max. (C\geq0.1\muF) \\ W.V.: 16V/10V: 0.125max. \\ W.V.: 6.3V: 0.15max. \\ \end{array}$	frequency and Char. Item Frequency Voltage	voltage shown ΔC to ΔU, 1X (1000pF and below) 1±0.1MHz 0.5 to 5Vrms	AC to ΔU, 1X (more than 1000pF) R6, R7, F5 B1, B3, F1 1±0.1kHz 1±0.2Vrms	E4 1±0.1kHz 0.5±0.05Vrms

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		·	ications	_	-		
No. I	tem	Temperature Compensating Type	High Dielectric Type		Test Meth	nod	
	Appearance	No defects or abnormalities					
	Capacitance	Within the specified tolerance					
11 Vibration Resistance	Q/D.F.	30pF and over : Q≥1000 30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	$\begin{array}{l} [B1, B3, R1, R6, R7, E4] \\ W.V.: 25Vmin.: 0.025max. \\ W.V.: 16/10V: 0.035max. \\ W.V.: 6.3V/4V \\ : 0.05max. (C<3.3\mu F) \\ : 0.1max. (C\geq3.3\mu F) \\ [F1, F5] \\ W.V.: 25Vmin. \\ : 0.05max. (C<0.1\mu F) \\ : 0.09max. (C\geq0.1\mu F) \\ W.V.: 16V/10V: 0.125max. \\ W.V.: 6.3V: 0.15max. \\ \end{array}$	Solder the capacitor on the test jig (glass epoxy board) in same manner and under the same conditions as (10). The capacitor should be subjected to a simple harmonic r having a total amplitude of 1.5mm, the frequency being va uniformly between the approximate limits of 10 and 55Hz frequency range, from 10 to 55Hz and return to 10Hz, sho be traversed in approximately 1 minute. This motion shou applied for a period of 2 hours in each 3 mutually perpend directions (total of 6 hours).			as (10). harmonic motion cy being varied and 55Hz. The 10Hz, should otion should be
		No crack or marked defect shou	uld occur	in Fig. 2a using direction shown	an eutectic solder.	Then apply ec. The sold	a force in the lering should be
12 Def 13 Soldera Termina		R230	45	$\begin{array}{c c c c c c c c c c c c c c c c c c c $		c 0.3 0.5 1.2 1.65 2.0 2.9 3.7 5.6 (in mm) JIS-K-8101) and on) .	
	Appearance	No defects or abnormalities					
	Capacitance Change	Within $\pm 2.5\%$ or ± 0.25 pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±7.5% F1, F5, E4 : Within ±20%	Immerse the cap	acitor at 120 to 150 pacitor in an eutecti nds. Set at room te	c solder sol	ution at 270±5℃
Resistance to Soldering Heat	Q/D.F.	30pF and over : Q≧1000 30pF and below : Q≧400+20C C : Nominal Capacitance (pF) More than 10,000MΩ or 500Ω •	 [B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max. W.V.: 6.3V/4V : 0.05max. (C<3.3µF) : 0.1max. (C≥3.3µF) [F1, F5] W.V.: 25Vmin. : 0.05max. (C<0.1µF) : 0.09max. (C≥0.1µF) W.V.: 16V/10V: 0.125max. W.V.: 6.3V: 0.15max. 	(temperature con constant type), t •Initial measurer Perform a heat t	mpensating tyoe) o hen measure. ment for high dielec reatment at 150+0, temperature for 48 al measurement.	r 48±4 hour tric constan /–10°C for o ±4 hours.	rs (high dielectrie t type
		wore than 10,000M\Omega or 500 Ω ·	 r (vvnicnever is smaller) 				
	Dielectric	No defects					

Continued on the following page. \square

Capacitors muRata

I.R.

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			Specifi	cations						
N	o. Ite	em	Temperature Compensating Type	High Dielectric Type	Test Method					
			The measured and observed ch specifications in the following ta							
		Appearance	No defects or abnormalities							
		Capacitance Change	Within $\pm 2.5\%$ or ± 0.25 pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±7.5% F1, F5, E4 : Within ±20%	Perform the five cycles according to the four heat				atments	
				[B1, B3, R1, R6, R7, E4] W.V. : 25Vmin. : 0.025max. W.V. : 16/10V : 0.035max.	Set for 24±2 h hours (high die measure.					
1	Temperature		30pF and over : Q≧1000	W.V. : 6.3V/4V	Step	1	2	3	4	
	Cycle	Q/D.F.	30pF and below : Q≧400+20C	: 0.05max. (C<3.3µF) : 0.1max. (C≧3.3µF) [F1, F5]	Temp. (℃)	Min. Operating Temp.+0/-3	Room Temp.	Max. Operating Temp.+3/-0	Room Temp.	
			C : Nominal Capacitance (pF)	W.V. : 25Vmin.	Time (min.)	30±3	2 to 3	30±3	2 to 3	
			· · · · · · · · · · · · · · · · · · ·	: 0.05max. (C<0.1µF) : 0.09max. (C≧0.1µF) W.V. : 16V/10V : 0.125max. W.V. : 6.3V : 0.15max.	 Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour and then set at room temperature for 48±4 hours. Perform the initial measurement. 					
		I.R.	More than 10,000M\Omega or 500Ω			5111.				
		Dielectric Strength	No defects							
			The measured and observed ch specifications in the following ta							
		Appearance	No defects or abnormalities							
		Capacitance Change	Within ±5% or ±0.5pF (Whichever is larger)	B1, B3, R1, R6, R7, C8 : Within ±12.5% F1, F5 : Within ±30%						
1	Humidity 6 (Steady State)	Q/D.F.	30pF and over : $Q \ge 350$ 10pF and over 30pF and below : $Q \ge 275+2.5C$ 10pF and below : $Q \ge 200+10C$ C : Nominal Capacitance (pF)	$\begin{array}{l} [B1, B3, R1, R6, R7, E4] \\ W.V.: 25Vmin.: 0.05max. \\ W.V.: 16/10V: 0.05max. \\ W.V.: 6.3V/4V \\ : 0.075max. (C<3.3\muF) \\ : 0.125max. (C\geq3.3\muF) \\ [F1, F5] \\ W.V.: 25Vmin. \\ : 0.075max. (C<0.1\muF) \\ : 0.125max. (C\geq0.1\muF) \\ W.V.: 16V/10V: 0.15max. \\ W.V.: 6.3V: 0.2max. \\ \end{array}$	Set the capacitor at 40±2°C and in 90 to 95% humidu 500±12 hours. Remove and set for 24±2 hours (temperature compet type) or 48±4 hours (high dielectric constant type) at temperature, then measure.		ensating			

More than 1,000M Ω or 50 Ω • F (Whichever is smaller)

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			Specif	cations	
No.	Ite	em	Temperature Compensating Type	High Dielectric Type	Test Method
			The measured and observed ch specifications in the following ta		
		Appearance	No defects or abnormalities		
		Capacitance Change	Within ±7.5% or ±0.75pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±12.5% F1, F5, E4 : Within ±30% [W.V. : 10Vmax.] F1, F5 : Within +30/-40%	Apply the rated voltage at 40±2°c and 90 to 95% humidity for 500±12 hours. Remove and set for 24±2 hours (temperature
17	Humidity Load	Q/D.F.	30pF and over : Q≥200 30pF and below : Q≥100+10C/3 C : Nominal Capacitance (pF)	$\begin{array}{l} [B1, B3, R1, R6, R7, E4] \\ W.V.: 25Vmin.: 0.05max. \\ W.V.: 16/10V: 0.05max. \\ W.V.: 6.3V \\ : 0.075max. (C<3.3\muF) \\ : 0.125max. (C\geq3.3\muF) \\ [F1, F5] \\ W.V.: 25Vmin. \\ : 0.075max. (C<0.1\muF) \\ : 0.125max. (C\geq0.1\muF) \\ W.V.: 16V/10V: 0.15max. \\ W.V.: 6.3V: 0.2max. \\ \end{array}$	 compensating type) or 48±4 hours (high dielectric constant type) at room temprature, then muasure. The charge/discharge current is less than 50mA. Initial measurement for F1, F5/10V max. Apply the rated DC voltage for 1 hour at 40±2°C. Remove and set for 48±4 hours at room temperature. Perform initial measurement.
		I.R.	More than 500M Ω or 25 Ω • F (V	Vhichever is smaller)	
			The measured and observed ch specifications in the following ta		
		Appearance	No defects or abnormalities		
		Capacitance Change	Within ±3% or ±0.3pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±12.5% F1, F5, E4 : Within ±30% [Exept 10Vmax. and. C≧1.0μF] F1, F5 : Within +30/−40% [10Vmax. and. C≧1.0μF]	Apply 200% of the rated voltage at the maximum operating temperature ±3°C for 1000±12 hours. Set for 24±2 hours (temperature compensating type) or 48±4 hours (high dielectric constant type) at room
18	High Temperature Load	perature		$\begin{array}{l} [B1, B3, R1, R6, R7, E4] \\ W.V.: 25Vmin.: 0.04max. \\ W.V.: 16/10V: 0.05max. \\ W.V.: 6.3V \\ : 0.075max.(C<3.3\mu F) \\ : 0.125max.(C\geq3.3\mu F) \\ [F1, F5] \\ W.V.: 25Vmin. \\ : 0.075max.(C<0.1\mu F) \\ : 0.125max.(C\geq0.1\mu F) \\ : 0.125max.(C\geq0.1\mu F) \\ W.V.: 16V/10V: 0.15max. \\ W.V.: 6.3V: 0.2max. \\ \end{array}$	 temperature, then measure. The charge/discharge current is less than 50mA. Initial measurement for high dielectric constant type. Apply 200% of the rated DC voltage at the maximun operating temperature ±3° for one hour. Remove and set for 48±4 hours at room temperature. Perform initial measurement.
		I.R.	More than 1,000M Ω or 50 Ω •F (Whichever is smaller)	

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Table A-1

		Capacitance Change from 25°C (%)						
Char.	Nominal Values (ppm/℃)*1	-55		-	-30		-10	
		Max.	Min.	Max.	Min.	Max.	Min.	
5C	0± 30	0.58	-0.24	0.40	-0.17	0.25	-0.11	
6C	0± 60	0.87	-0.48	0.59	-0.33	0.38	-0.21	
6P	-150± 60	2.33	0.72	1.61	0.50	1.02	0.32	
6R	-220± 60	3.02	1.28	2.08	0.88	1.32	0.56	
6S	-330± 60	4.09	2.16	2.81	1.49	1.79	0.95	
6T	-470± 60	5.46	3.28	3.75	2.26	2.39	1.44	
7U	-750±120	8.78	5.04	6.04	3.47	3.84	2.21	
1X	+350 to -1000	-	-	-	-	-	-	

*1Nominal values denote the temperature coefficient within a range of 25°C to 125°C (for Δ C)/85°C (for other TC).

10	۱۱
(2	-)

			(Capacitance Cha	inge from 20℃ (%)		
Char.	Nominal Values (ppm/℃)*2	_	-55	-	-25		10
		Max.	Min.	Max.	Min.	Max.	Min.
2C	0± 60	0.82	-0.45	0.49	-0.27	0.33	-0.18
3C	0±120	1.37	-0.90	0.82	-0.54	0.55	-0.36
4C	0±250	2.56	-1.88	1.54	-1.13	1.02	-0.75
2P	-150 ± 60	_	_	1.32	0.41	0.88	0.27
3P	-150±120	_	_	1.65	0.14	1.10	0.09
4P	-150 ± 250	_	_	2.36	-0.45	1.57	-0.30
2R	-220 ± 60	_	_	1.70	0.72	1.13	0.48
3R	-220±120	_	_	2.03	0.45	1.35	0.30
4R	-220 ± 250	_	_	2.74	-0.14	1.83	-0.09
2S	-330 ± 60	_	_	2.30	1.22	1.54	0.81
3S	-330±120	_	_	2.63	0.95	1.76	0.63
4S	-330 ± 250	_	_	3.35	0.36	2.23	0.24
2T	-470 ± 60	_	_	3.07	1.85	2.05	1.23
3T	-470±120	_	_	3.40	1.58	2.27	1.05
4T	-470±250	_	_	4.12	0.99	2.74	0.66
3U	-750±120	_	_	4.94	2.84	3.29	1.89
4U	-750±250	_	_	5.65	2.25	3.77	1.50

*2Nominal values denote the temperature coefficient within a range of 20°C to 125°C (for Δ C)/85°C (for other TC).

Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

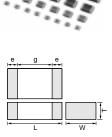
High Dielectric Constant Type 100V

Part Number	TC Code	Rated Voltage (Vdc) Capacitance*		Length L (mm)	Width W (mm)	Thickness T (mm)
GRM188R72A222KD01	X7R (EIA)	100	2200pF±10%	1.6	0.8	0.80
GRM188R72A332KD01	X7R (EIA)	100	3300pF±10%	1.6	0.8	0.80
GRM219R72A472KA01	X7R (EIA)	100	4700pF±10%	2.0	1.25	0.90
GRM219R72A682KA01	X7R (EIA)	100	6800pF±10%	2.0	1.25	0.90
GRM21BR72A103KA01	X7R (EIA)	100	10000pF±10%	2.0	1.25	1.25
GRM31MR72A333KA01	X7R (EIA)	100	33000pF±10%	3.2	1.6	1.15
GRM31MR72A473KA01	X7R (EIA)	100	47000pF±10%	3.2	1.6	1.15
GRM32NR72A683KA01	X7R (EIA)	100	68000pF±10%	3.2	2.5	1.35
GRM32NR72A104KA01	X7R (EIA)	100	0.1µF±10%	3.2	2.5	1.35
GRM43RR72A154KA01	X7R (EIA)	100	0.15µF±10%	4.5	3.2	1.80
GRM43RR72A224KA01	X7R (EIA)	100	22000pF±10%	4.5	3.2	1.80
GRM43DR72A474KA01	X7R (EIA)	100	0.47µF±10%	4.5	3.2	2.00
GRM55DR72A105KA01	X7R (EIA)	100	1μF ±10%	5.7	5.0	2.00
GRM188F52A472ZD01	Y5V (EIA)	100	4700pF +80%, -20%	1.6	0.8	0.80
GRM32NF52A104ZA01	Y5V (EIA)	100	10000pF +80%, -20%	3.2	2.5	1.35
GRM55RF52A474ZA01	Y5V (EIA)	100	0.47µF +80%, -20%	5.7	5.0	1.80

Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

Thin Layer Large-Capacitance type

Part Number	Dimensions (mm)					
Fait Nulliber	L	W	Т	e min.	g min.	-
GRM033	0.6 ±0.03	0.3 ±0.03	0.3 ±0.03	0.1 to 0.2	0.2	
GRM155	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4	
GRM185	1.6 ±0.1	0.8 ±0.1	0.5 +0/-0.2	0.2 to 0.5	0.5	
GRM188	1.6 ±0.1	0.8 ±0.1	0.8 ±0.1	0.2 to 0.5	0.5	
GRM216			0.6 ±0.1			
GRM219	2.0 ±0.1	1.25 ±0.1	0.85 ±0.1	0.2 to 0.7	0.7	
GRM21B			1.25 ±0.1			
GRM316			0.6 ±0.1			
GRM319	3.2 ±0.15	1.6 ±0.15	0.85 ±0.1	0.3 to 0.8	1.5	e g
GRM31M	1		1.15 ±0.1	0.3 10 0.8	1.5	++ + × +
GRM31C	3.2 ±0.2	1.6 ±0.2	1.6 ±0.2			
GRM32D	3.2 ±0.3	25102	2.0 ±0.2	0.3	10	
GRM32E	3.2 ±0.3	2.5 ±0.2	2.5 ±0.2	0.3	1.0	
GRM43D			2.0 ±0.2			
GRM43E	4.5 ±0.4	3.2 ±0.3	2.5 ±0.2	0.3	2.0	
GRM43S	1		2.8 ±0.2			1 4 L
GRM55F	5.7 ±0.4	5.0 ±0.4	3.2 ±0.2	0.3	2.0	



Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R60J154KE01	X5R (EIA)	6.3	0.15µF±10%	1.0	0.5	0.50
GRM155R60J224KE01	X5R (EIA)	6.3	22000pF±10%	1.0	0.5	0.50
GRM155R60J334KE01	X5R (EIA)	6.3	0.33 μF±10%	1.0	0.5	0.50
GRM155R60J474KE19	X5R (EIA)	6.3	0.47µF±10%	1.0	0.5	0.50
GRM188R60J225KE01	X5R (EIA)	6.3	2.2μF ±10%	1.6	0.8	0.80
GRM219R60J475KE01	X5R (EIA)	6.3	4.7μF ±10%	2.0	1.25	0.90
GRM21BR60J106KE01	X5R (EIA)	6.3	10μF ±10%	2.0	1.25	1.25
GRM21BR60J106ME01	X5R (EIA)	6.3	10μF ±20%	2.0	1.25	1.25
GRM32DR60J226KA01	X5R (EIA)	6.3	22μF ±10%	3.2	2.5	2.00
GRM32ER60J476ME20	X5R (EIA)	6.3	47μF ±20%	3.2	2.5	2.50
GRM43SR60J107ME20	X5R (EIA)	6.3	100μF ±20%	4.5	3.2	2.80
GRM55FR60J107KA01	X5R (EIA)	6.3	100μF ±10%	5.7	5.0	3.20
GRM55FR60J107MA01	X5R (EIA)	6.3	100μF ±20%	5.7	5.0	3.20
GRM21BF50J106ZE01	Y5V (EIA)	6.3	10μF +80%, -20%	2.0	1.25	1.25

No.	Ite	em	Specifications		Tes	st Method			
1	Operating Temperat Range		B1, B3, F1 : -25°C to +85°C R6 : -55°C to +85°C F5 : -30°C to +85°C C8 : -55°C to +105°C, C7 : -55°C to +125°C	Reference Temperature : 25°C (B1, B3, F1 : 20°C)					
2	2 Rated Voltage See the previous pages		See the previous pages	The rated voltage is defined as the maximum voltage which may be applied continuously to the capacitor. When AC voltage is superimposed on DC voltage, V ^{p.p} or V ^{o.p} , whichever is larger, should be maintained within the rated voltage range.					
3	Appearar	nce	No defects or abnormalities	Visual inspection					
4	Dimensio	ons	Within the specified dimensions	Using calip	oers				
5	Dielectric	c Strength	No defects or abnormalities	No failure should be observed when 250% of the rated voltage is applied between the terminations for 1 to 5 seconds, provided the charge/discharge current is less than 50mA.					
6	Insulatior Resistanc		More than 50Ω • F	The insulation resistance should be measured with a not exceeding the rated voltage at Reference Temper 75%RH max. and within 1 minutes of charging, provid charge/discharge current is less than 50mA.			ice Temperature and ging, provided the		
			Within the specified tolerance	The capacitance should be measured at Reference Temperature at the frequency and voltage shown in the f					
7	7 Capacitance		*Table 1 Capacitance GRM155 B3/R6 1A 124 to 224 C≦10µF (10V min.) ³ GRM185 B3/R6 1A 105 C≦10µF (6.3V max. GRM188 B3/R6 1C/1A 225 C>10µF GRM219 B3/R6 1A 475 *1 However the Volt GRM21B B3/R6 1C/1A 106 items on the left statement		μF (10V min.)*1 μF (6.3V max.) μF		1.0±0.2Vrms 0.5±0.1Vrms 0.5±0.1Vrms		
			B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max.	The D.F. should be measured at Reference Temperature at the frequency and voltage shown in the table.					
8	Dissipatio (D.F.)	on Factor	*Table 1 GRM155 B3/R6 1A 124 to 224 GRM185 B3/R6 1A 105 GRM188 B3/R6 1C/1A 225 GRM219 B3/R6 1A 475 GRM21B B3/R6 1C/1A 106	C≦10µF (10V min.)* ¹ 1±0.1kHz 1.0±0.2Vr C≦10µF (6.3V max.) 1±0.1kHz 0.5±0.1Vr			1.0±0.2Vrms 0.5±0.1Vrms 0.5±0.1Vrms		
		No bias	Io bias each specifie I_1 , B_3 : Within +/-10% (-25°c to +85°c) The ranges of F_1 : Within +30/-80% (-25°c to +85°c) Reference Te R_6 : Within +/-15% (-55°c to +85°c) shown in the F_5 : Within +22/-82% (-30°c to +85°c) In case of ap C_7 : Within +/-22% (-55°c to +125°c) measured aft C_8 : Within +/-22% (-55°c to +105°c) equilibration of			he capacitance change should be measured after 5min. at ach specified temp. stage. he ranges of capacitance change compared with the eference Temperature value over the temperature ranges nown in the table should be within the specified ranges.* case of applying voltage, the capacitance change should be easured after 1 more min. with applying voltage in quilibration of each temp. stage. GRM43 B1/R6 0J/1A 336/476 only : 1.0±0.2Vrms			
				Step	Temperature		Applying Voltage (V)		
9	Capacitance Temperature			2	Reference Tem -55±3 (for R6 -25±3 (for B -30±3 (for	pereture±2 5, C7, C8)/ 1, B3, F1)			
	Characteristics			3	Reference Tem	,	No bias		
		50% of		4	85±3 (for B1, B3 125±3 (fo	, F1, R6, F5) or C7)/			
		the Rated	B1: Within +10/-30% F1: Within +30/-95%		105±3 (fo				
		Voltage	1 1. WIGHT TOU-30%	5	20±2				
				6	-25±3 (for		50% of the rated		
				7	20±2		voltage		
				8	85±3 (for E				
				Perform a then set fo	asurement for high heat treatment at r 48±4 hours at ro e initial measurem	150 +0/-10° oom temperat	C for one hour and		

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No.	Item	Specifications		Test Me	Test Method			
		No removal of the terminations or other defects should occur	Solder the capacitor on the test jig (glass epoxy board) shown in Fig. 1a using an eutectic solder. Then apply $10N^*$ force in parallel with the test jig for $10+/-1$ sec. The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is uniform and free of defects such as heat shock. *5N : GR \Box 15/GRM18, 2N : GR \Box 33					
	Adhesive Strength		Туре	а	b	С		
10	of Termination		GR□03	0.3	0.9	0.3		
			GR□15	0.4	1.5	0.5		
		VA VA VA VA VA Solder resist	GRM18	1.0	3.0	1.2		
		Baked electrode or	GRM21	1.2	4.0	1.65		
		copper foil	GRM31	2.2	5.0	2.0		
			GRM32	2.2	5.0	2.9		
		Fig. 1a	GRM43	3.5	7.0	3.7		
			GRM55	4.5	8.0	5.6		
			GRIVISS	4.5	0.0	5.0		
11	Appearance Capacitance Vibration D.F.	No defects or abnormalities Within the specified tolerance B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max. No cracking or marking defects should occur	Solder the capacitor on the test jig (glass epoxy board) in the same manner and under the same conditions as (10). The capacitor should be subjected to a simple harmonic mo- having a total amplitude of 1.5mm, the frequency being vari- uniformly between the approximate limits of 10 and 55Hz. T frequency range, from 10 to 55Hz and return to 10Hz, should be traversed in approximately 1 minute. This motion should applied for a period of 2 hours in each 3 mutually perpendic directions (total of 6 hours). Solder the capacitor on the test jig (glass epoxy board) show					
		20 speed : 1.0mm/sec. Pressunze Pressunze Flexure : ≤1	direction shown in be done either with should be conduct and free of defects	n an iron or usi ed with care so	ng the reflow m that the solde	nethod and ring is uniform		
12	Deflection	Capacitance meter		Fig. 2	а	t : 1.6mm		
					(GR□03, GR	□15 : t : 0.8mm)		
			Туре	а	b	С		
		Fig.3a	GR□03	0.3	0.9	0.3		
			 GR□15	0.4	1.5	0.5		
			GRM18	1.0	3.0	1.2		
			GRM21	1.2	4.0	1.65		
			GRM31	2.2	5.0	2.0		
			GRM31 GRM32	2.2	5.0	2.9		
				3.5	7.0	3.7		
			<u>GRM43</u> GRM55	4.5	7.0	<u> </u>		
			GRIVISS	4.5	0.0	(in mm)		
						. /		
13	Solderability of Termination	75% of the terminations is to be soldered evenly and continuously	Immerse the capa rosin (JIS-K-5902) Preheat at 80 to 12 After preheating, in 2+/-0.5 seconds	(25% rosin in 20℃ for 10 to 3 mmerse in an e	weight propotic 0 seconds.	on) .		

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Continued from the preceding page.

No.	Ite	Item Specifications			Test Method						
		Appearance Capacitance Change Q/D.F.	No defects or abnormalities B1, B3, R6, C7, C8 : Within ±7.5% F1, F5 : Within ±20% B1, B3, R6, C7, C8 : 0.1 max.	Im 27 24	Preheat the capacitor at 120 to 150°C for 1 minute. Immerse the capacitor in an eutectic solder solution at 270+/-5°C for 10+/-0.5 seconds. Set at room temperature for 24+/-2 hours (temperature compensating type) or 48+/-4 hours (high dielectric constant type), then measure.						
14	Resistance to Soldering Heat		F1, F5 : 0.2 max.	•Ir	nitial measu	rement for high	dielectri	c constant type			
		I.R. Dielectric Strength	More than 50Ω • F No defects	Pe the	 Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour and then set at room temperature for 48+/-4 hours. Perform the initial measurement. 						
				*P	reheating fo	or GRM32/43/5	5				
					Step	Temp	erature	Т	ime		
					1 2	100℃ 170℃		min. min.			
		Appearance	No defects or abnormalities					in the same m	anner and		
		Capacitance Change	B1, B3, R6, C7, C8 : Within ±7.5% F1, F5 : Within ±20%	Pe	under the same conditions as (10). Perform the five cycles according to the four heat treatments						
		D.F.	B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max.	Se	 shown in the following table. Set for 24+/-2 hours (temperature compensating type) or 48+/-4 hours (high dielectric constant type) at room 						
		I.R.	More than 50Ω • F	te	mperature, f	then measure.					
15	Temperature Sudden	Dielectric Strength	No defects		Step	1 Min.	2 Deem	3 Max.	4		
	Change -				Temp. (℃)	Operating Temp. +0/-3	Room Temp.	Operating Temp. +3/-0	Room Temp.		
		Appearance	No defects or abnormalities	the Pe	 Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour a then set at room temperature for 48+/-4 hours. Perform the initial measurement. Apply the rated voltage at 40+/-2°C and 90 to 95% hum 						
	High Temperature High Humidity (Steady)	Capacitance Change	B1, B3, R6, C7, C8 : Within ±12.5% F1, F5 : Within ±30%	50	500+/12 hours. The charge/discharge currentis less than 50mA.						
16		D.F. I.R.	B1, B3, R6, C7, C8 : 0.2 max. F1, F5 : 0.4 max. More than 12.5Ω • F	Pe th	 Initial measurement Perform a heat treatment at 150+0/-10°C for one hour and then let sit for 48+/-4 hours at room temperature. Perform th initial measurement. Measurement after test Perform a heat treatment at 150+0/-10°C for one hour and then let sit for 48+/-4 hours at room temperature, then measure. 						
				Pe th							
		Appearance	No defects or abnormalities				-	000+/12 hou			
17	Durability	Capacitance Change	B1, B3, R6, C7, C8 : Within ±12.5% F1, F5 : Within ±30%	hc	 maximum operating temperature +/-3°C. Let sit for 48 hours at room temperature, then measure. The charge/ discharge current is less than 50mA. 				+0〒/一4		
		D.F.	B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.4 max.	•Ir	Initial measurement						
		I.R.	More than 25Ω • F	the		48+/-4 hours		10°C for one ho temperature. P			
				Pe th		at treatment at		10℃ for one ho temperature, th			